Abstract
(from international publication)

The invention relates to a magnetron sputtering process that allows material to be sputtered from a target surface in such a way that a high percentage of the sputtered material is provided in the form of ions. According to the invention, said aim is achieved using a simple generator, the power of which is fed to multiple magnetron sputtering sources spread out over several time intervals, i.e. the maximum power is supplied to one sputtering source during one time interval, and the maximum power is supplied to the following sputtering source in the subsequent time interval, such that discharge current densities of more than 0.2A/cm^2 are obtained. The sputtering target can cool down during the off time, thus preventing the temperature limit from being exceeded.

Text in the figures

Figure	Original text	English-language translation
4	Pulsleistung (2x)	pulse power
5	Erfindungsgemäss	according to the invention
	Wellenlänge	wave length
6	Multipuls	multi-pulse
	Wellenlänge	wave length